

# Easy B series

AIM Zhou Yizheng



Never stop thinking

# Overview

## ■ Voltage class

□ 600V

□ 1200V

## ■ Current

□ 600V up to 200A

□ 1200V up to 150A

“Easy2 (Y)”



“Easy1 (X)”



“Easy1B (W1)”



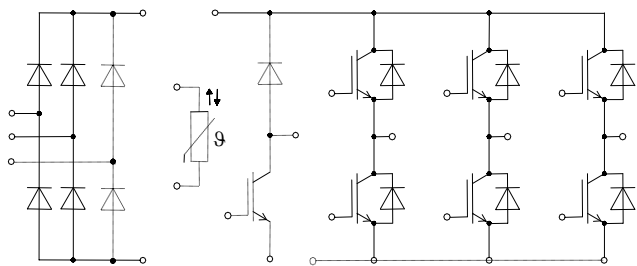
“Easy2B (W2)”



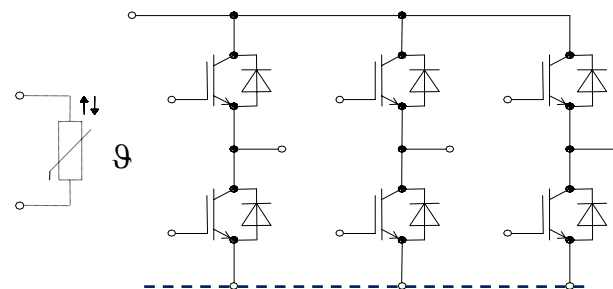
“Easy750 (V)”



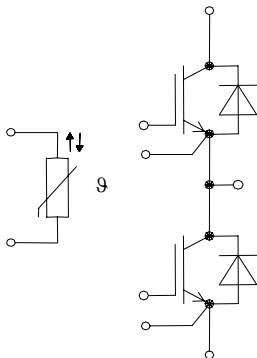
# Circuit Configuration



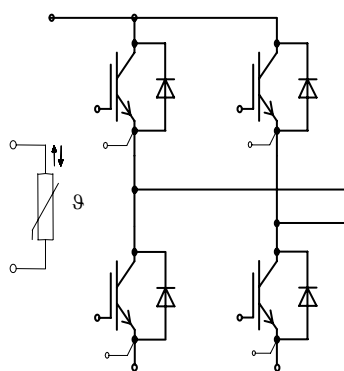
**"EasyPIM"**  
FP/FB



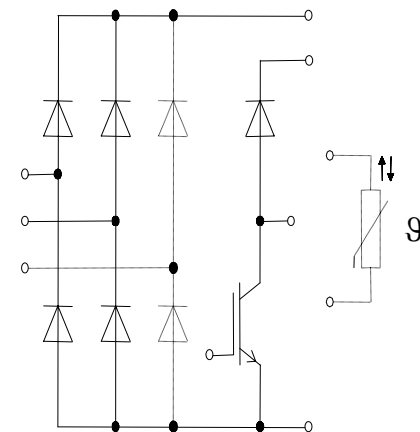
**"EasyPACK"**  
FS



**"EasyDUAL"**  
FF



**"EasyFourPACK"**  
F4



**"EasyBridge"**  
DD

# Chip technology

- 1200V Trench Field Stop
- T3 Easy1B
- T4 (Latest) Easy1B, Easy2B
- 20% Lower Switch losses than T3 with the same switching characteristics ;
- Operational junction temperature  $T_{vj.op}=150^{\circ}\text{C}$  ;
- The robustness with same SC withstand time;
- 600V
- E3 Trench Field Stop Easy1B
- $T_{vj.max}=175^{\circ}\text{C}$ ,  $T_{vj.op}=150^{\circ}\text{C}$  ;
- SC time 6us;
- KL4 NPT

# Mechanical Construction

★ **Without Base Plate**  
(Cost Saving & Compact)

Double Cu-layer  
DCB Substrate  
(Thermal Conduction &  
2.5 kV Isolation)

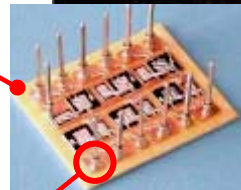
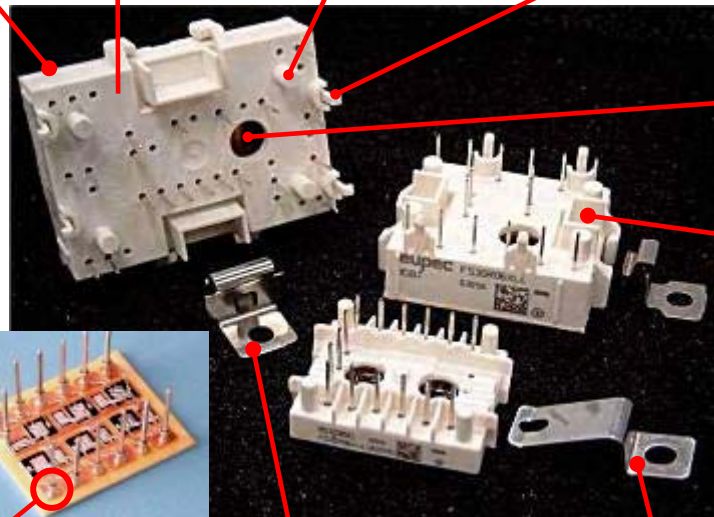
★ **Pin-rivet Connection**  
(Low Contact Ohm &  
Process Automation)

Distance  
Bolts

Hooks (for  
Wave Soldering)

Hole (Filling in Soft Gel)

Notches  
(Clamp Fitting)



★ **Mounted with Clamps**  
(Adapting to Plastic Deformation &  
Holding Mounting Force)

# Mechanical Construction of Easy B series

**Without Base Plate**  
(Cost Saving & Compact)

★ **Module height is 12mm**  
Same with Easy750  
Easy1, Easy2 height is 17mm

**Pin-rivet Connection**  
(Low Contact Ohm & Process Automation)



★ **No hooks**  
Connect PCB with screws or just by soldering

★ **Pin grid**  
for max. flexibility separately

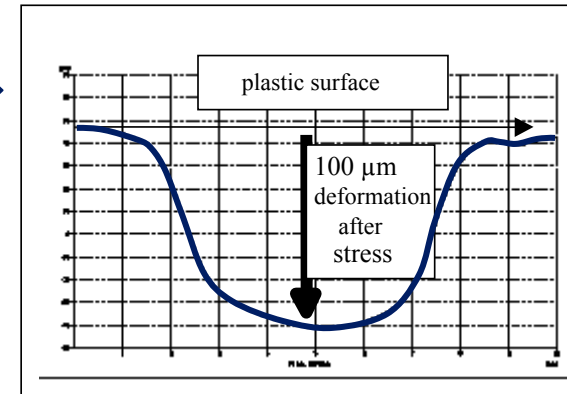
★ **Mounted with Clamps**  
The clamps is pre-assembled

★ **Protected ceramic**  
Like Easy750

# Why Clamping

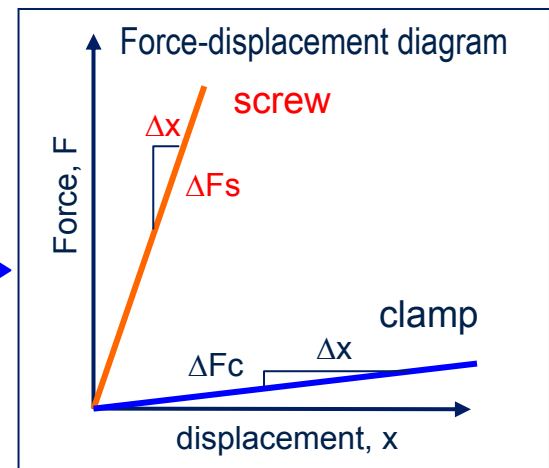
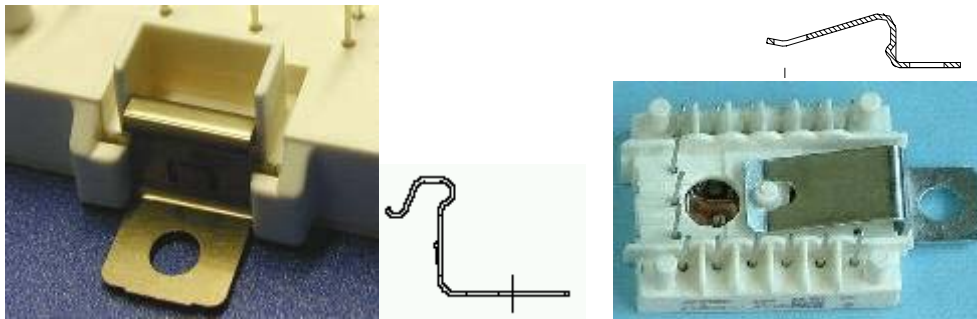


time,  
screwing  
force



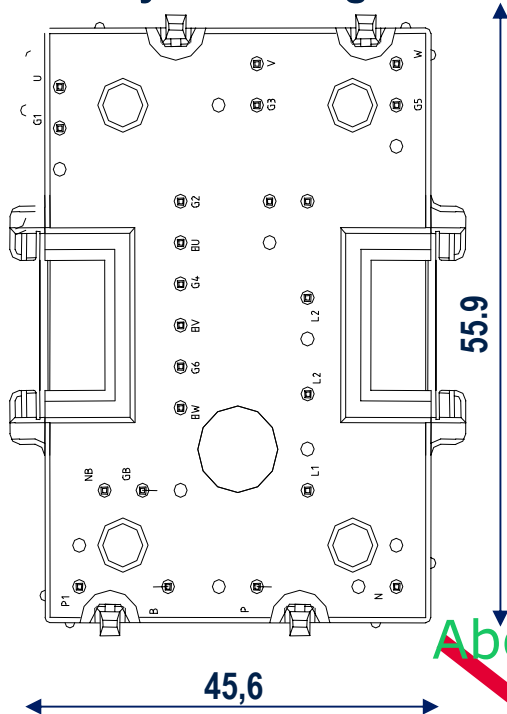
## Clamping Features

- Adapting to plastic deformation
- Holding & nearly mounting force constant over lifetime, Therefore keep better contact thermal resistance  $R_{\text{thch}}$ .
- DCB Safety – lower risk of Ceramics Cracks

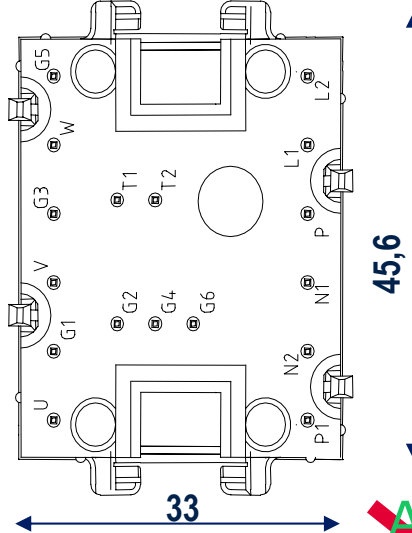


# Frame size

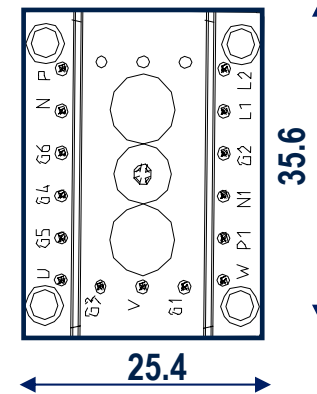
**Easy2 housing**



**Easy1 housing**



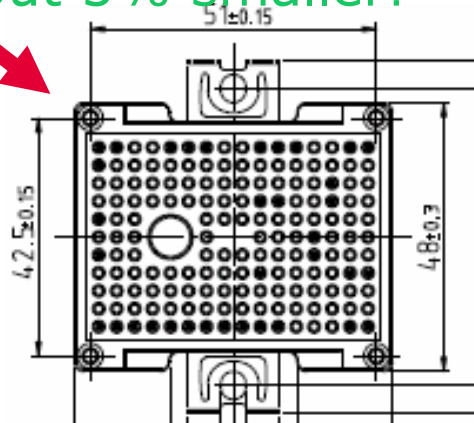
**Easy750 housing**



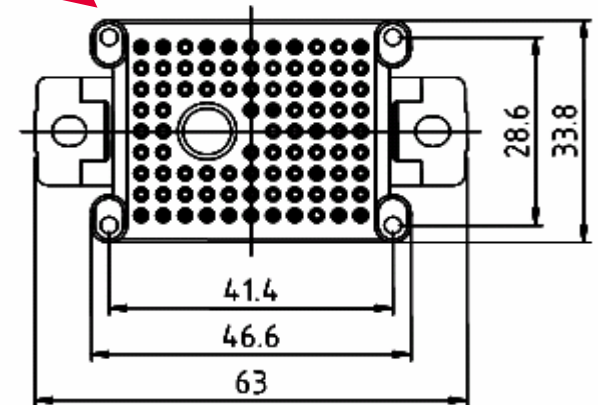
About 5% smaller!

About 7% smaller!

**Easy2B housing**



**Easy1B housing**



Dimensions in [mm]



# Easy™ Product Portfolio



# Type designation

**!! New indication for new housings !!**

- **W for Easy B series**

- An additional figure shows the footprint



# Easy1B

## EasyPIM™ module

□ 1200V

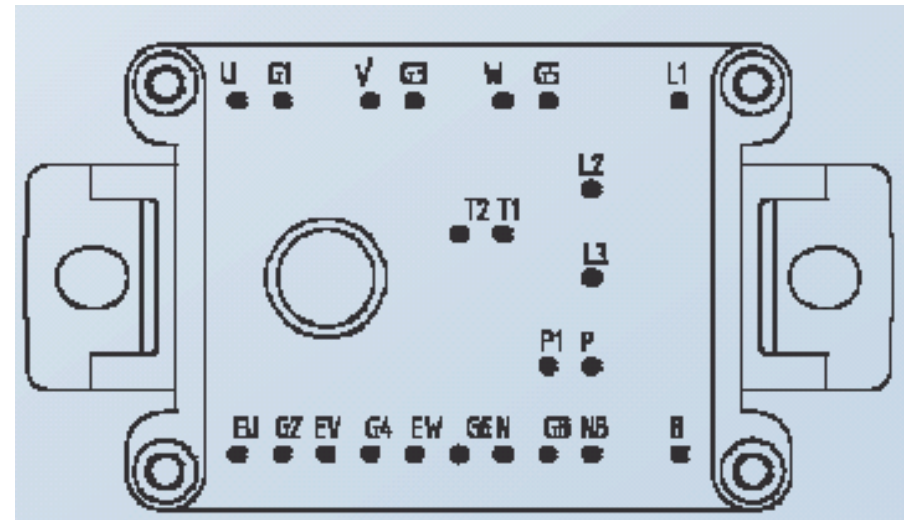
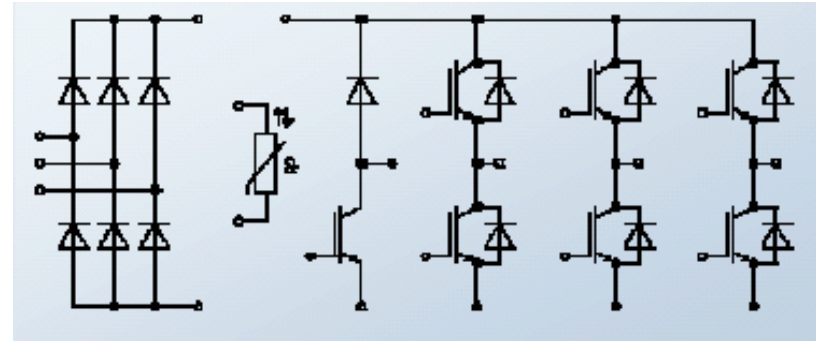
FP**10/15**R**12**W1**T3**

FP**06/10/15**R**12**W1**T4** (-B3)

□ 600V

FP**10/15/20/30**R**06**W1**E3**

FB**10/15/20/30**R**06**W1**E3**



***New 1200V IGBT4 inside!!***

**Current (A)** **Voltage (V)**

# Easy1B

## EasyPACK™ module

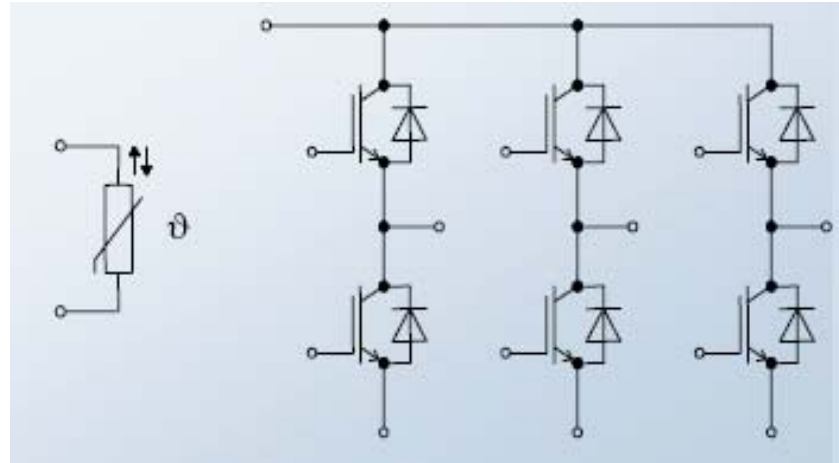
□ 1200V

FS**25**R**12**W1**T4**

FS**35**R**12**W1**T4**

□ 600V

FS**20/30/50**R**06**W1**E3**





# Easy2B

## EasyPIM™ module

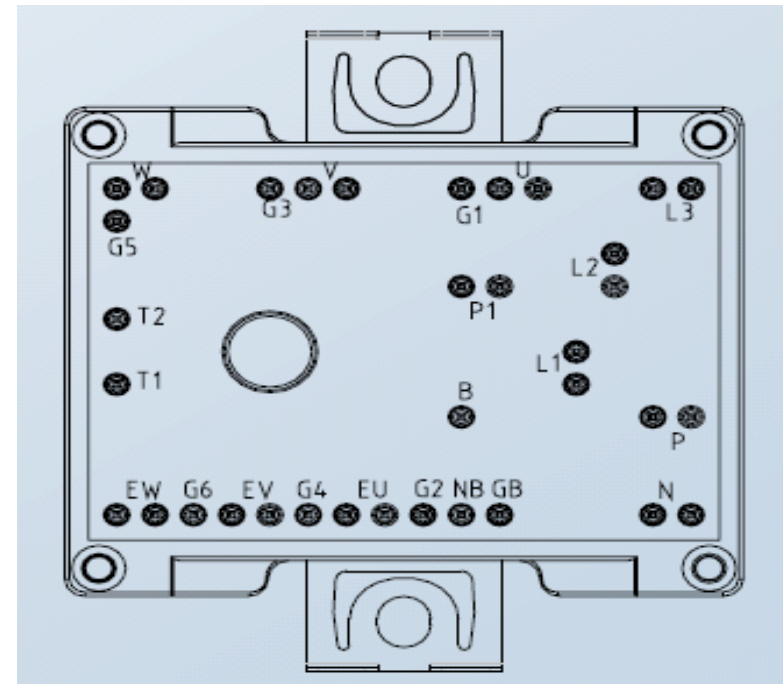
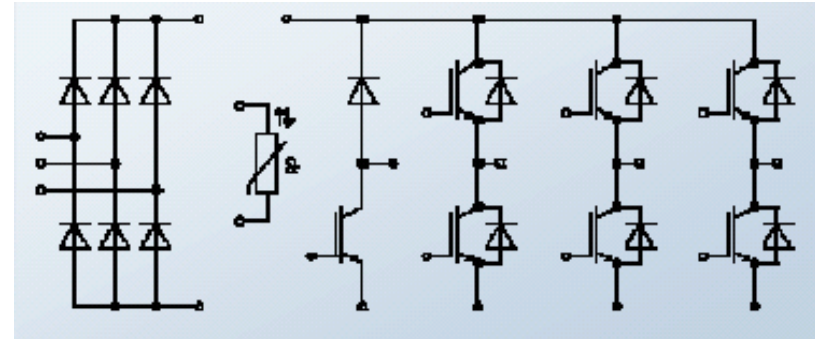
1200V  
 FP**25**R**12**W2**T4**  
 FP**35**R**12**W2**T4**

600V  
 FP**35**R**06**W2**E3**  
 FP**50**R**06**W2**E3**

Coming later

**1200V IGBT4 in new housing!!**

**Current (A) Voltage (V)**



# Easy2B

## EasyPACK™ module

□ 1200V

FS**50**R**12**W2**T4**

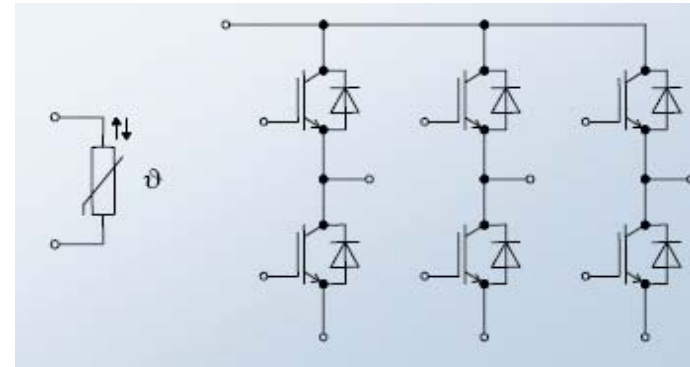
FS**75**R**12**W2**T4**

□ 600V

FS**50**R**06**W2**E3**

FS**75**R**06**W2**E3**

**Coming later**



**Current (A)** **Voltage (V)**

# Easy Portfolio



Easy1B



Easy2B



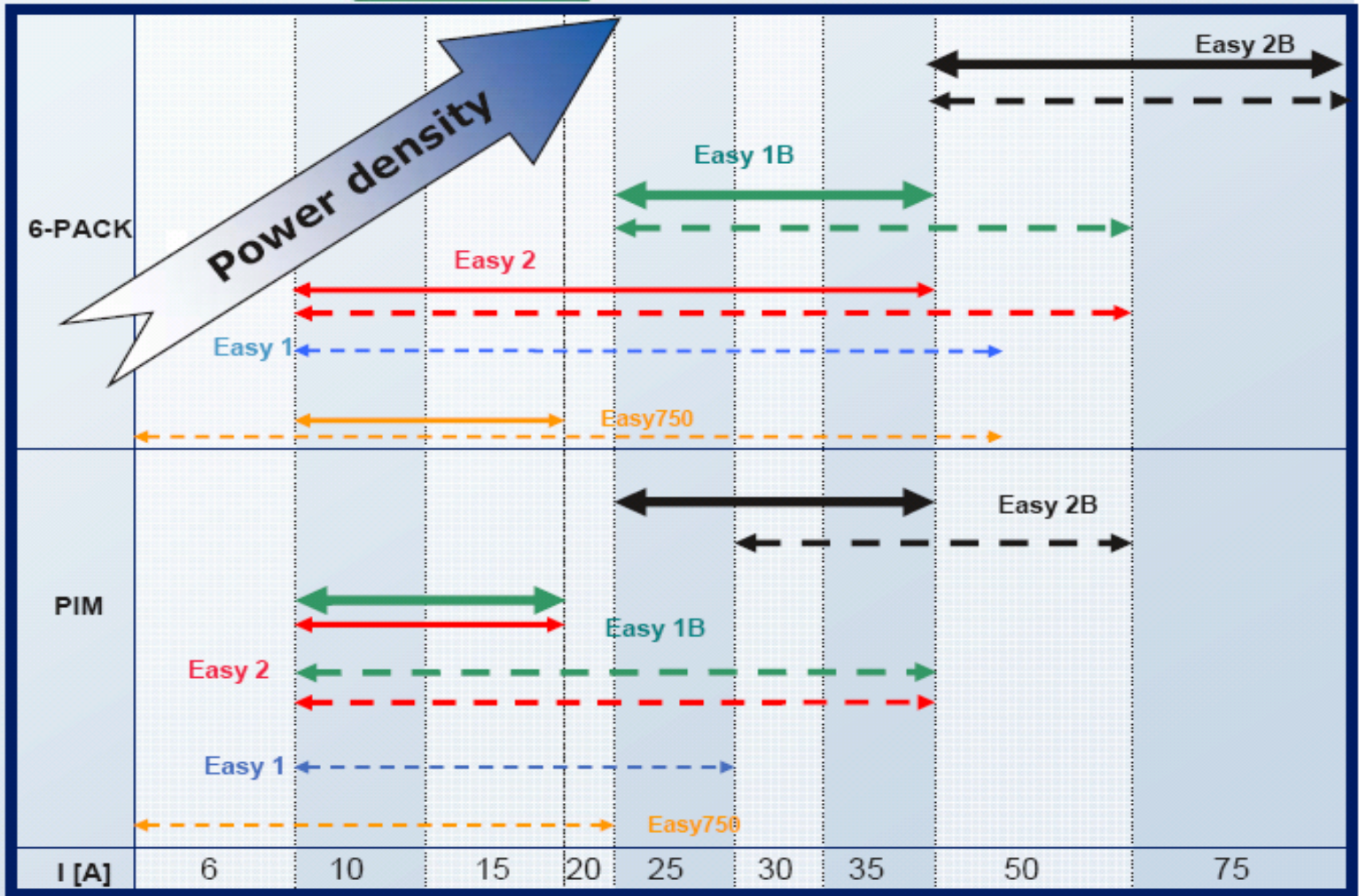
Easy2



Easy1



Easy750



**Legend:** 600V = - - - - - 1200V = ————

# Benchmark for 1200V 15A T4 vs.T3

Please specify your inverter application in the green layered fields:

application parameters:	simulation parameters:	limits:
DC link voltage $V_{dc}$ [V]	513	nom. voltage 600 V $\pm 20\%$
frequency $f_0$ [Hz]	50	480 V = $V_{dc}$ = 720 V
switching frequency $f_s$ [Hz]	8000 to 15000	1 Hz = $f_0$ = 1000 Hz
modulation factor $m$	1.14	5 x $f_0$ = $f_s$ = 10000 x $f_0$
$\cos \phi$	0.80	0 = $m$ = 4/p
		-1 = $\cos \phi$ = 1
max. ambient temperature $T_a$ [°C]	40	0 °C = $T_a$ = $T_h$

choose:

☒ IGBT ☐ Diode

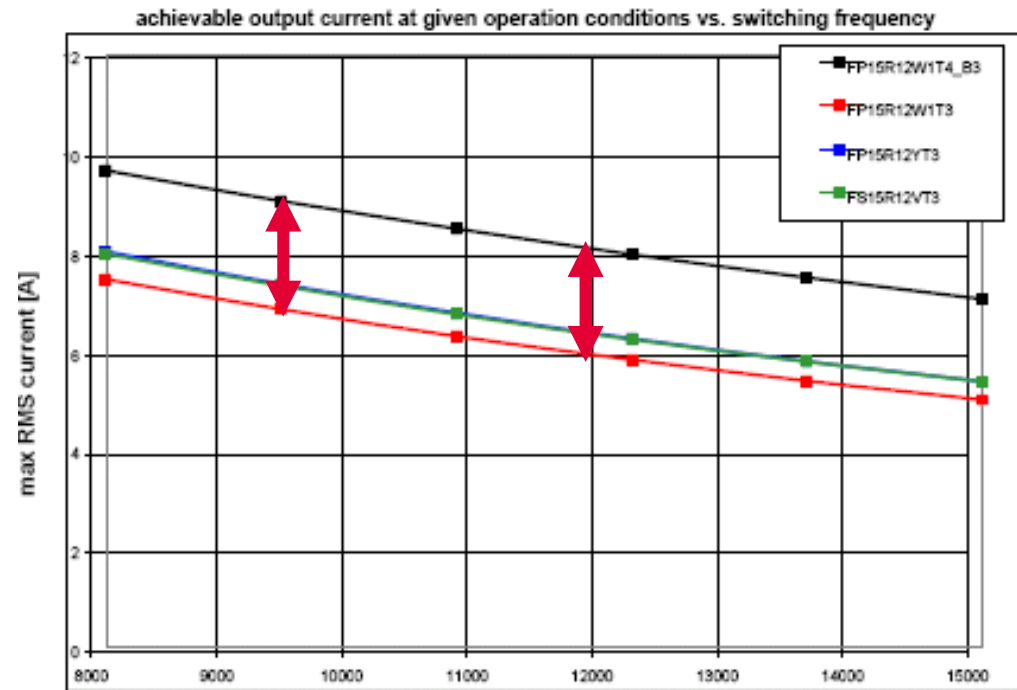


diagram based on typical device data

switching frequency  $f_s$  [Hz]

**Output current capability:**  
**T4 > T3!**

☒ IGBT
 ☐ Diode

select up to three modules for benchmark

	housing type	R <sub>th</sub> IGBT l-junction to heat sink	R <sub>th</sub> case to heat sink per IGBT [K/W]	R <sub>th</sub> heat sink per module arm [K/W]	max. junction temp. T <sub>j</sub> [°C]
FP15R12W1T4_B3	EasyPIM18	2.2000	0.000	4.400	150
FP15R12W1T3	EasyPIM18	2.2500	0.000	4.400	125
FP15R12YT3	EasyPIM2	1.8500	0.000	4.400	125
FS15R12VT3	EasyPACK750	2.0500	0.000	4.400	125



# Comparison of 2.2kW inverter

## Condition:

$I_{orms} = 5.5A$ ,  $V_{dc} = 513V$ ,  $f_{sw} = 14kHz$ ,  $OL = 150\%$ ,  $T_a = 40^\circ C$ ,

**$R_{thha}$  per arm = 4.4k/W**

## Module: EasyPIM™1B FP15R12W1T4 Vs. FP15R12W1T3

temperature distribution  
selected module

FP15R12W1T4\_B3

simulation parameters:		temperature at I <sub>rms</sub> = 6 A
DC link voltage V <sub>dc</sub> [V]	513	T <sub>Jmax</sub> [°C] 120.6
RMS current I <sub>rms</sub> [A]	5.5	T <sub>c</sub> [°C] 93.6
frequency f <sub>0</sub> [Hz]	50	T <sub>h</sub> [°C] 93.6
switching frequency f <sub>sw</sub> [Hz]	14000	
max. junction temperature T <sub>J</sub> [°C]	150	max. current for T <sub>J</sub> <= 150° C
modulation factor m	1.14	I <sub>rms</sub> [A] 7.4
cos φ	0.80	
R <sub>th</sub> IGBT-junction to heat sink [K/W]	2.2	choose: <input checked="" type="checkbox"/> IGBT <input type="checkbox"/> Diode
R <sub>th</sub> case to heat sink per arm [K/W]	0.000	<input type="text" value="0.000"/> <input type="text" value="0.000"/>

Please specify heat sink and ambient temperature in the green layered fields	application parameters:	
R <sub>th</sub> heat sink per arm [K/W]	4.400	
max. ambient temperature T <sub>a</sub> [°C]	40	0° C = T <sub>a</sub> = T <sub>h</sub>
static IGBT losses [W]	03	
dynamic IGBT losses [W]	06	Σ 09
static diode losses [W]	00	
dynamic diode losses [W]	02	Σ 02

temperature distribution  
selected module

FP15R12W1T3

simulation parameters:		temperature at I <sub>rms</sub> = 6 A
DC link voltage V <sub>dc</sub> [V]	513	T <sub>Jmax</sub> [°C] 128.4
RMS current I <sub>rms</sub> [A]	5.5	T <sub>c</sub> [°C] 99.1
frequency f <sub>0</sub> [Hz]	50	T <sub>h</sub> [°C] 99.1
switching frequency f <sub>sw</sub> [Hz]	14000	
max. junction temperature T <sub>J</sub> [°C]	125	max. current for T <sub>J</sub> <= 125° C
modulation factor m	1.14	I <sub>rms</sub> [A] 5.3
cos φ	0.80	
R <sub>th</sub> IGBT-junction to heat sink [K/W]	2.25	choose: <input checked="" type="checkbox"/> IGBT <input type="checkbox"/> Diode
R <sub>th</sub> case to heat sink per arm [K/W]	0.000	<input type="text" value="0.000"/> <input type="text" value="0.000"/>

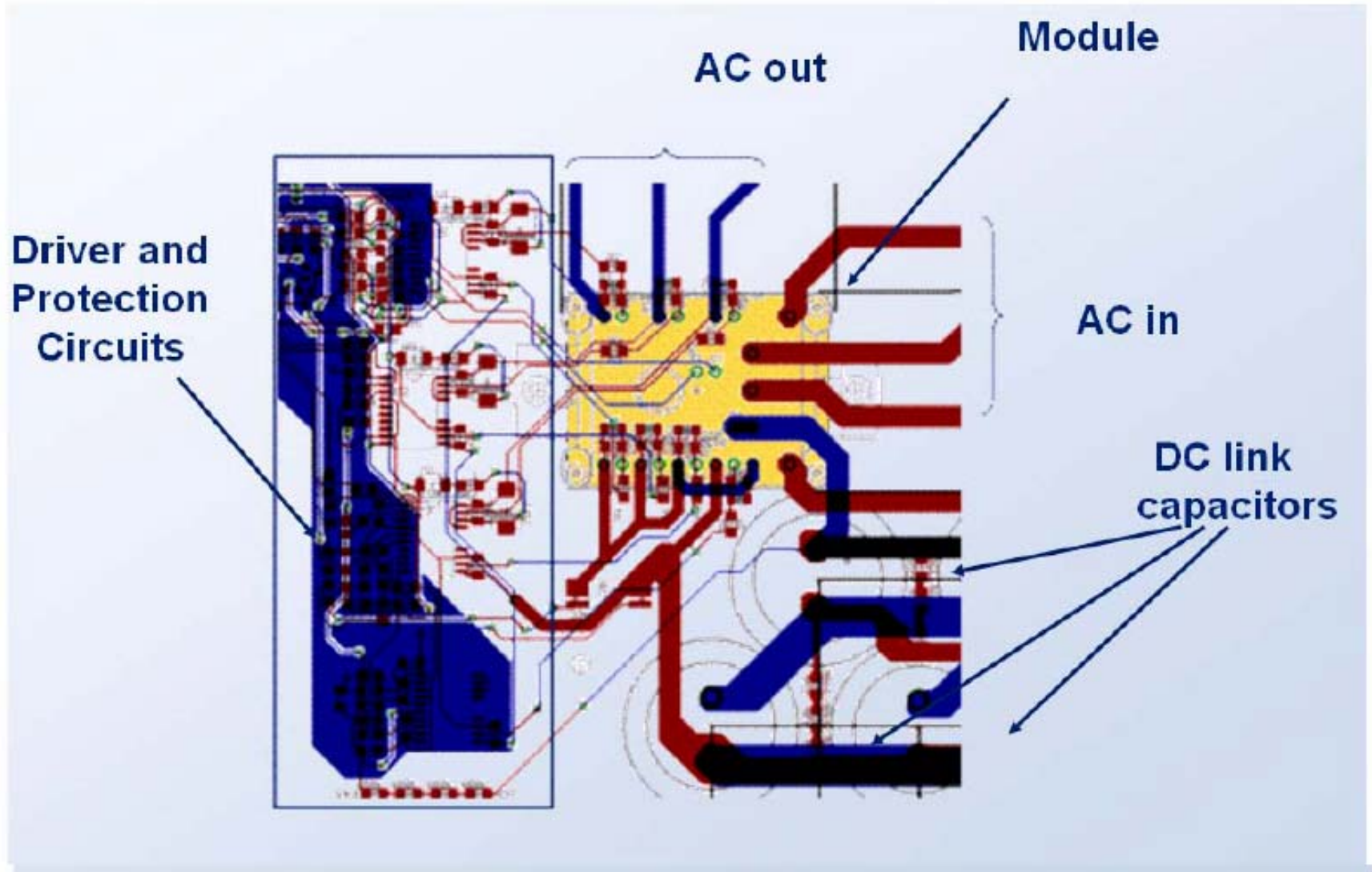
Please specify heat sink and ambient temperature in the green layered fields	application parameters:	
R <sub>th</sub> heat sink per arm [K/W]	4.400	
max. ambient temperature T <sub>a</sub> [°C]	40	0° C = T <sub>a</sub> = T <sub>h</sub>
static IGBT losses [W]	03	
dynamic IGBT losses [W]	07	Σ 10
static diode losses [W]	00	
dynamic diode losses [W]	03	Σ 03

### Simulation results:

Heatsink **T<sub>h</sub>**  
T<sub>4</sub>(93.6°C) < T<sub>3</sub> (99.1°C)

Operational **T<sub>vj</sub>**  
T<sub>4</sub> (120.6°C) < T<sub>3</sub> (128.4°C)

# Possible layout for FP15R12W1T3



# System reference layout

## Possible Inverter Design with FP15R12W1T3

### A very compact Inverter Design!

